

# FSA8039 Audio Jack Detection and Configuration Switch with Moisture Sensing

### Features

Detection	Accessory Plug-In 3-Pole or 4-Pole Audio Jack Send / End Key Pressed Moisture
Switch Type	MIC
V <sub>DD</sub>	2.5 V to 4.5 V
V <sub>IO</sub>	1.6 to V <sub>DD</sub>
THD (MIC)	0.01% Typical
ESD (Air Gap)	15 kV
Operating Temperature	-40°C to 85°C
Package	10-Lead UMLP, 1.4 mm × 1.8 mm × 0.5 mm, 0.4 mm Pitch
Top Mark	NF
Ordering	FSA8039UMSX-F106
Information	FSA8039AUMSX-F106

# Applications

- 3.5 mm and 2.5 mm Audio Jacks
- Cellular Phones, Smart Phones
- MP3 and PMP

# Description

The FSA8039 is an audio jack detection switch for 3-pole and 4-pole accessories. The FSA8039 features moisture sensing, which prevents false positive detection of accessories in the audio jack. The FSA8039 also features an integrated MIC switch that allows a processor to configure attached accessories. The architecture is designed to allow common third-party headphones to be used for listening to music from mobile handsets, personal media players, and portable peripheral devices.

- Prevents False Detection of Accessories in the Audio Jack when Moisture is Present
- Removes Audio Jack Pop & Click Caused by MIC Bias
- Detects Audio Jack Accessories:
  - Standard Headphones
  - Send / End Button Presses
- Integrates a MIC Switch for 4-Pole Configuration

#### **Related Resources**

FSA8039 Evaluation Board





Note:

1. L=LOW, H=HIGH.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Param	Min.	Max.	Unit		
V <sub>DD</sub> , V <sub>IO</sub>	DC Supply Voltages		-0.5	6.0	V	
Vsw	MIC Switch I/O Voltage and All Input V	oltages Except J_DET	-0.5	V <sub>DD</sub> +0.5	V	
V <sub>JD</sub>	Input Voltage for J_DET Input		-1.5	V <sub>DD</sub> +0.5	V	
V <sub>SW-JMIC</sub>	J-MIC Maximum Voltage Across V $_{\rm DD}$ F	Range <sup>(2)</sup>		6	V	
lıк	Input Clamp Diode Current		-50		mA	
Isw	Switch I/O Current (Continuous) <sup>(3)</sup>			150	mA	
T <sub>STG</sub>	Storage Temperature Range			+150	°C	
TJ	Maximum Junction Temperature			+150	°C	
TL	Lead Temperature (Soldering, 10 Seconds)			+260	°C	
	IEC 61000-4-2 System ESD	Air Gap	15.0			
		Contact	8.0		kV	
ESD	Human Body Model, JEDEC JESD22-A114,	$J\_DET, J\_MIC, V_{DD}, V_{IO}, GND$	13.0			
		All Other Pins	8.0			
	Charged Device Model, JEDEC JESD22-C101	All Pins	2.0			

Notes:

2. Maximum voltage on J-MIC and MIC pins for a maximum of 30 minutes,  $V_{DD}$  2.5 to 4.5 V. Sw itch can be open or closed.

3. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.

# **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
V <sub>DD</sub>	Battery Supply Voltage	2.5	4.5	V
V <sub>IO</sub>	Parallel I/O Supply Voltage	1.6	V <sub>DD</sub>	V
TA	Operating Temperature	-40	+85	٥C

### CONFIDENTIAL AND PROPRIETARY - DO NOT DISTRIBUTE

# **DC Electrical Characteristics**

All typical values are at  $T_A=25^{\circ}C$  unless otherwise specified.

O. makes I	Denomination		O an diti an	T <sub>A</sub> =-40 to +85°C			1.1
Symbol	Parameter	V <sub>DD</sub> (V)	Condition	Min.	Тур.	Max.	Unit
MIC Switch			•	4	1	•	
V <sub>IN</sub>	Switch Input Voltage Range	2.5 to 4.5		0		V <sub>DD</sub>	V
		2.8			0.85	2.00	
Ron	MIC Switch On Resistance	3.0	lout=30 mA, Vin=2 2 V		0.70	2.00	
		3.8	V IN-2.2 V		0.40	2.00	
		2.8			0.45	1.50	Ω
R <sub>FLAT(ON)</sub>	On Resistance Flatness	3.0	$I_{OUT}=30 \text{ mA},$		0.40	1.50	
. ,		3.3	V IN=1.0 10 2.0 V		0.35	1.50	4
J_DET	I			1			
J_DET <sub>AudioV</sub>	Audio Voltage on J_DET Pin	2.5 to 4.5	DET=LOW	-1		1	V
J_DET <sub>Audiof</sub>	Audio Frequency on J_DET Pin <sup>(4)</sup>	2.5 to 4.5	DET=LOW	20		20000	Hz
J_DET <sub>RGND</sub>	Detection Resistance to Ground	2.5 to 4.5	Audio Accessory Inserted	0		500	kΩ
J_DET <sub>HYS</sub>	Hysteresis of J_DET				200		mV
J_DET <sub>VIH</sub>	J_DET Input High Voltage			0.7 × V <sub>DD</sub>		V <sub>DD</sub>	V
J_DET <sub>VIL</sub>	J_DET Input Low Voltage			-1		0.4 × V <sub>DD</sub>	V
Parallel I/O	•					•	
VIH	EN Input High Voltage			0.7 × V <sub>IO</sub>		V <sub>IO</sub>	
VIL	EN Input Low Voltage					0.3 × V <sub>IO</sub>	V
V <sub>OH</sub>	DET, S/E Output High Voltage		I <sub>ОН</sub> =-100 µА	0.8 × V <sub>IO</sub>			
V <sub>OL</sub>	DET, S/E Output Low Voltage		l <sub>o∟=+</sub> 100 µA			0.2 × V <sub>IO</sub>	
Comparato	r						
Vcomp_s/e	Comparator Threshold for SEND/END Sensing	2.8 to 4.5	J_DET, EN=LOW		780		mV
Current				•			
loff	Pow er-Off Leakage Current Through Switch	0	MIC=4.3 V			1	μΑ
lın	Input Leakage Current	0	EN=4.3 V			1	μA
ICC-SLNA	V <sub>DD</sub> Supply Sleep Mode Current (No Accessory Attached)	2.5 to 4.5	EN=LOW		1.5	3.0	μA
ICC-SLWA	V <sub>DD</sub> Supply Active Mode Current (Accessory Attached)	2.5 to 4.5	DET=LOW, EN=HIGH		20	30	μA

Note:

4. Limits based on electrical characterization data.

### CONFIDENTIAL AND PROPRIETARY - DO NOT DISTRIBUTE

# **AC Electrical Characteristics**

All typical values are for V\_{CC}=3.3 V at T\_A=25 ^{\circ}C unless otherwise specified.

Symbol	Parameter	V <sub>DD</sub> (V)	Conditions	Typical	Unit	
MIC Switch						
THD+N	Total Harmonic Distortion + Noise <sup>(5)</sup>	3.8	R <sub>T</sub> =600 Ω, f=20 Hz to 20 kHz, $V_{MIC}$ =2.2 VDC + 0.5V <sub>PP</sub> Sine	0.01	%	
O <sub>IRR</sub>	Off Isolation <sup>(5)</sup>	3.8	f=20 Hz to 20 kHz, $R_S=R_T=32 \Omega$ , $C_L=0 pF$	-85	dB	
C <sub>ON</sub>	MIC and J_MIC Switch ON Capacitance <sup>(5)</sup>	3.8	f=1 MHz	60	pF	
COFF	MIC and J_MIC Switch OFF Capacitance <sup>(5)</sup>	3.8	f=1 MHz	35	pF	
Parallel I/	0		•			
t <sub>R</sub> , t <sub>F</sub>	Output Edge Rates (DET, S/E)	3.8	C <sub>L</sub> =5 pF, 20% to 80%,	20	ns	
tpoll	On Time of MIC Switch for Sensing SEND/END Button Press	2.5 to 4.5	DET= LOW, EN= LOW	1	ms	
twait	Period of MIC Switching Time for Sensing SEND/END Button Press	2.5 to 4.5	DET= LOW, EN= LOW	10	ms	
t <sub>DET_IN</sub>	Debounce Time after J_DET Changes State from HIGH to LOW	2.5 to 4.5		70	ms	
tdet_rem	Debounce Time after J_DET Changes State from LOW to HIGH	2.5 to 4.5		30	μs	
t <sub>квк</sub>	SEND/END Button Press/Release Debounce Time	2.5 to 4.5		30	ms	
Power						
PSRR	Pow er Supply Rejection Ratio <sup>(5)</sup>	3.8	Pow er Supply Noise 300 mV $_{PP}$ , f=217 Hz	-90	dB	

Note:

5. Limits based on electrical characterization data.

# Application Information

#### **Design/Layout Best Practices**

System-level Electrostatic Discharge (ESD) events often occur in the audio path of a mobile device, typically when inserting or removing an accessory from the audio jack. The audio path from the audio jack to the audio codec or microphone pre-amplifier is typically designed for relatively low frequencies (<100 kHz). How ever, an ESD event is a high-frequency event with fast edge rates (<100 ns/V). Because of this, the audio signal paths represent a high-frequency transmission line to the ESD signal.

Use the following PCB design and layout best practices when designing a system audio path.

#### Audio Path Layout Guidelines for ESD

For the MIC and ground signals between the audio jack and FSA8039, decrease the spacing between these traces to increase the inductive coupling of these signals. In effect, this creates a low-frequency bandpass filter that shunts ESD energy to ground before it reaches internal components. Where feasible, lay the MIC trace as a shielded stripline; an example is show n in Figure 4.



Figure 4. MIC PCB Trace as Shielded Stripline

#### **Ground Layout Guidelines**

Ground layout for audio path devices should consider high-frequency effects. During an ESD event, parasitic inductance and resistance in the ground path reduces its ability to shunt the fast transient energy. Use the follow ing techniques to improve grounding effectiveness:

- Use "star" ground connections (not daisy-chain).
- Use ground vias to minimize ground path impedance and ground loops.
- Stitch ground traces to the ground plane at the device, where possible (see Figure 4).
- Flood ground; where possible (see Figure 4).
- Avoid ground "islands" or "peninsulas" if possible.
- If using a modular audio jack assembly that is not soldered to the main PCB, use a ground pad on the jack with an ohmic connection to battery ground.





In addition to ESD robustness, these techniques can improve audio signal performance by reducing audio cross-talk and echo due to resistive voltage drops in the audio ground path.

#### CONFIDENTIAL AND PROPRIETARY - DO NOT DISTRIBUTE





 Table 1.
 Nominal Values

JEDEC Symbol	Description	Nominal Values (mm)
A	Overall Height	0.5
A1	Package Standoff	0.026
A3	Lead Thickness	0.152
b	Lead Width	0.2
L	Lead Length	0.4
e	Lead Pitch	0.4
D	Body Length (Y)	1.8
E	Body Width (X)	1.4





ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage maybe accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury of the part. ON Semiconductor is an Equal Opportunit/Affirmative Action Employer. This literature is subject to

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada.

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semic onductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative